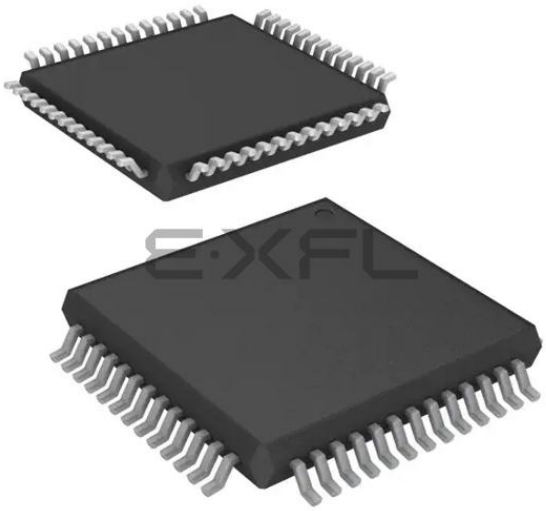
Renesas Electronics America Inc - R5F2135CCDFP#30 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	47
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 12x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	52-LQFP
Supplier Device Package	52-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2135ccdfp-30

1.3 Block Diagram

Figure 1.2 shows a Block Diagram.

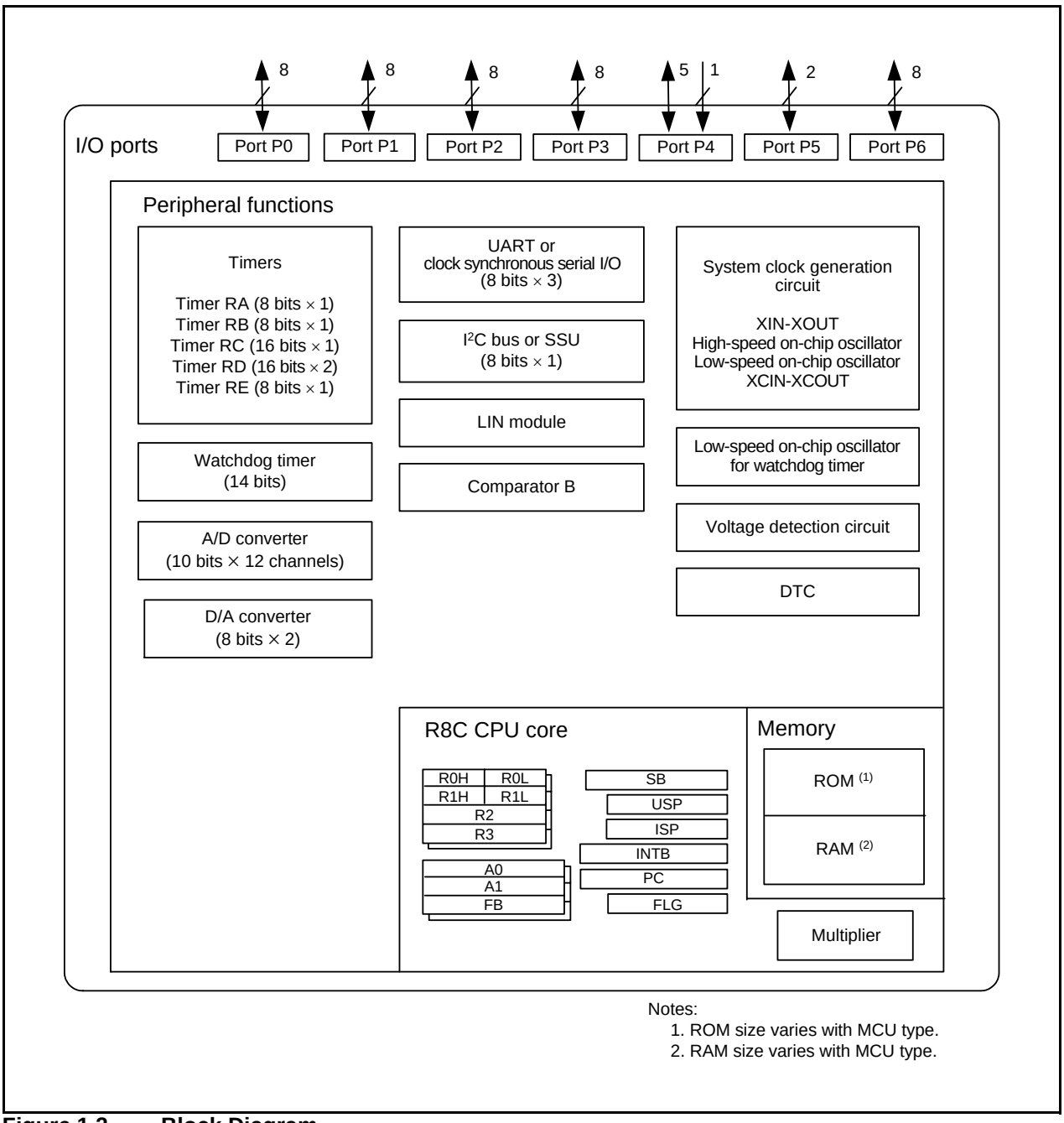


Figure 1.2 Block Diagram

Table 1.5 Pin Name Information by Pin Number (2)

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator B
36		P1_2	$\overline{KI2}$	(TRCIOB)				AN10
37		P1_1	$\overline{KI1}$	(TRCIOA/ TRCTRG)				AN9
38		P1_0	$\overline{KI0}$	(TRCIOD)				AN8
39		P0_7		(TRCIOC)				AN0/DA1
40		P0_6		(TRCIOD)				AN1/DA0
41		P0_5		(TRCIOB)				AN2
42		P0_4		TREO (/TRCIOB)				AN3
43		P0_3		(TRCIOB)	(CLK1)			AN4
44		P0_2		(TRCIOA/ TRCTRG)	(RXD1)			AN5
45		P0_1		(TRCIOA/ TRCTRG)	(TXD1)			AN6
46		P0_0		(TRCIOA/ TRCTRG)				AN7
47		P6_4			(RXD1)			
48		P6_3			(TXD1)			
49		P6_2			(CLK1)			
50		P6_1						
51		P6_0		(TREO)				
52		P5_7						

Note:
1. Can be assigned to the pin in parentheses by a program.

1.5 Pin Functions

Tables 1.6 and 1.7 list Pin Functions.

Table 1.6 Pin Functions (1)

Item	Pin Name	I/O Type	Description
Power supply input	VCC, VSS	–	Apply 1.8 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	–	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins (1). To use an external clock, input it to the XOUT pin and leave the XIN pin open.
XIN clock output	XOUT	I/O	
XCIN clock input	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins (1). To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$ to $\overline{\text{INT4}}$	I	$\overline{\text{INT}}$ interrupt input pins. $\overline{\text{INT0}}$ is timer RB, RC and RD input pin.
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAIO	I/O	Timer RA I/O pin
	TRAO	O	Timer RA output pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Timer RC I/O pins
Timer RD	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1	I/O	Timer RD I/O pins
	TRDCLK	I	External clock input pin
Timer RE	TREO	O	Divided clock output pin
Serial interface	CLK0, CLK1, CLK2	I/O	Transfer clock I/O pins
	RXD0, RXD1, RXD2	I	Serial data input pins
	TXD0, TXD1, TXD2	O	Serial data output pins
	$\overline{\text{CTS2}}$	I	Transmission control input pin
	$\overline{\text{RTS2}}$	O	Reception control output pin
	SCL2	I/O	I^2C mode clock I/O pin
	SDA2	I/O	I^2C mode data I/O pin
I^2C bus	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
SSU	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin

I: Input O: Output I/O: Input and output

Note:

1. Refer to the oscillator manufacturer for oscillation characteristics.

Table 1.7 Pin Functions (2)

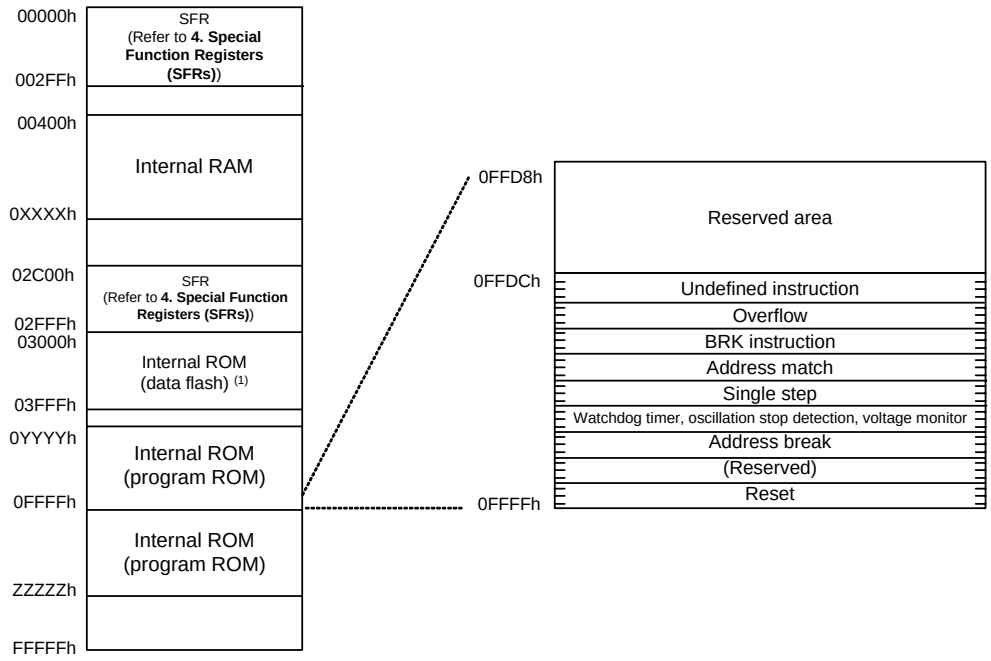
Item	Pin Name	I/O Type	Description
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter and D/A converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
	$\overline{\text{ADTRG}}$	I	A/D external trigger input pin
D/A converter	DA0, DA1	O	D/A converter output pins
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins
	IVREF1, IVREF3	I	Comparator B reference voltage input pins
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_7, P5_6, P5_7, P6_0 to P6_7	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. All ports can be used as LED drive ports.
Input port	P4_2	I	Input-only port

I: Input O: Output I/O: Input and output

3. Memory

3.1 R8C/35C Group

Figure 3.1 is a Memory Map of R8C/35C Group. The R8C/35C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 32-Kbyte internal ROM area is allocated addresses 08000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM area is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21354CNFP, R5F21354CDFP	16 Kbytes	0C000h	–	1.5 Kbytes	009FFh
R5F21355CNFP, R5F21355CDFP	24 Kbytes	0A000h	–	2 Kbytes	00BFFh
R5F21356CNFP, R5F21356CDFP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh
R5F21357CNFP, R5F21357CDFP	48 Kbytes	04000h	–	4 Kbytes	013FFh
R5F21358CNFP, R5F21358CDFP	64 Kbytes	04000h	13FFFh	6 Kbytes	01BFFh
R5F2135ACNFP, R5F2135ACDFP	96 Kbytes	04000h	1BFFFh	8 Kbytes	023FFh
R5F2135CCNFP, R5F2135CCDFP	128 Kbytes	04000h	23FFFh	10 Kbytes	02BFFh

Figure 3.1 Memory Map of R8C/35C Group

Table 4.4 SFR Information (4) (1)

Address	Register	Symbol	After Reset
00C0h	A/D Register 0	AD0	XXh
00C1h			000000XXb
00C2h	A/D Register 1	AD1	XXh
00C3h			000000XXb
00C4h	A/D Register 2	AD2	XXh
00C5h			000000XXb
00C6h	A/D Register 3	AD3	XXh
00C7h			000000XXb
00C8h	A/D Register 4	AD4	XXh
00C9h			000000XXb
00CAh	A/D Register 5	AD5	XXh
00CBh			000000XXb
00CCh	A/D Register 6	AD6	XXh
00CDh			000000XXb
00CEh	A/D Register 7	AD7	XXh
00CFh			000000XXb
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Mode Register	ADMOD	00h
00D5h	A/D Input Select Register	ADINSEL	11000000b
00D6h	A/D Control Register 0	ADCON0	00h
00D7h	A/D Control Register 1	ADCON1	00h
00D8h	D/A0 Register	DA0	00h
00D9h	D/A1 Register	DA1	00h
00DAh			
00DBh			
00DCh	D/A Control Register	DACON	00h
00DDh			
00DEh			
00DFh			
00E0h	Port P0 Register	P0	XXh
00E1h	Port P1 Register	P1	XXh
00E2h	Port P0 Direction Register	PD0	00h
00E3h	Port P1 Direction Register	PD1	00h
00E4h	Port P2 Register	P2	XXh
00E5h	Port P3 Register	P3	XXh
00E6h	Port P2 Direction Register	PD2	00h
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h	Port P5 Register	P5	XXh
00EAh	Port P4 Direction Register	PD4	00h
00EBh	Port P5 Direction Register	PD5	00h
00ECh	Port P6 Register	P6	XXh
00EDh			
00EEh	Port P6 Direction Register	PD6	00h
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h			
00F9h			
00FAh			
00FBh			
00FCh			
00FDh			
00FEh			
00FFh			

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

Table 4.7 SFR Information (7) (1)

Address	Register	Symbol	After Reset
0180h	Timer RA Pin Select Register	TRASR	00h
0181h	Timer RB/RC Pin Select Register	TRBRCSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h	Timer RD Pin Select Register 0	TRDPSR0	00h
0185h	Timer RD Pin Select Register 1	TRDPSR1	00h
0186h	Timer Pin Select Register	TIMSR	00h
0187h			
0188h	UART0 Pin Select Register	U0SR	00h
0189h	UART1 Pin Select Register	U1SR	00h
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU/IIC Pin Select Register	SSUIICSR	00h
018Dh			
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register (2)	SSTDR / ICDRT	FFh
0195h	SS Transmit Data Register H (2)	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register (2)	SSRDR / ICDRR	FFh
0197h	SS Receive Data Register H (2)	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 (2)	SSCRH / ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 (2)	SSCRL / ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register (2)	SSMR / ICMR	00010000b / 00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register (2)	SSER / ICIER	00h
019Ch	SS Status Register / IIC bus Status Register (2)	SSSR / ICSR	00h / 0000X000b
019Dh	SS Mode Register 2 / Slave Address Register (2)	SSMR2 / SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	00h
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:
1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.10 SFR Information (10) (1)

Address	Register	Symbol	After Reset
2C70h	DTC Control Data 6	DTCD6	XXh
2C71h			XXh
2C72h			XXh
2C73h			XXh
2C74h			XXh
2C75h			XXh
2C76h			XXh
2C77h			XXh
2C78h	DTC Control Data 7	DTCD7	XXh
2C79h			XXh
2C7Ah			XXh
2C7Bh			XXh
2C7Ch			XXh
2C7Dh			XXh
2C7Eh			XXh
2C7Fh			XXh
2C80h	DTC Control Data 8	DTCD8	XXh
2C81h			XXh
2C82h			XXh
2C83h			XXh
2C84h			XXh
2C85h			XXh
2C86h			XXh
2C87h			XXh
2C88h	DTC Control Data 9	DTCD9	XXh
2C89h			XXh
2C8Ah			XXh
2C8Bh			XXh
2C8Ch			XXh
2C8Dh			XXh
2C8Eh			XXh
2C8Fh			XXh
2C90h	DTC Control Data 10	DTCD10	XXh
2C91h			XXh
2C92h			XXh
2C93h			XXh
2C94h			XXh
2C95h			XXh
2C96h			XXh
2C97h			XXh
2C98h	DTC Control Data 11	DTCD11	XXh
2C99h			XXh
2C9Ah			XXh
2C9Bh			XXh
2C9Ch			XXh
2C9Dh			XXh
2C9Eh			XXh
2C9Fh			XXh
2CA0h	DTC Control Data 12	DTCD12	XXh
2CA1h			XXh
2CA2h			XXh
2CA3h			XXh
2CA4h			XXh
2CA5h			XXh
2CA6h			XXh
2CA7h			XXh
2CA8h	DTC Control Data 13	DTCD13	XXh
2CA9h			XXh
2CAAh			XXh
2CABh			XXh
2CACh			XXh
2CADh			XXh
2CAEh			XXh
2CAFh			XXh

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

Table 4.11 SFR Information (11) (1)

Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h			XXh
2CB4h			XXh
2CB5h			XXh
2CB6h			XXh
2CB7h			XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h			XXh
2CBAh			XXh
2CBBh			XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h			XXh
2CC3h			XXh
2CC4h			XXh
2CC5h			XXh
2CC6h			XXh
2CC7h			XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h			XXh
2CCAh			XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h			XXh
2CD3h			XXh
2CD4h			XXh
2CD5h			XXh
2CD6h			XXh
2CD7h			XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h			XXh
2CDAh			XXh
2CDBh			XXh
2CDCh			XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h			XXh
2CE5h			XXh
2CE6h			XXh
2CE7h			XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h			XXh
2CEAh			XXh
2CEBh			XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh

X: Undefined
Note:
1. The blank areas are reserved and cannot be accessed by users.

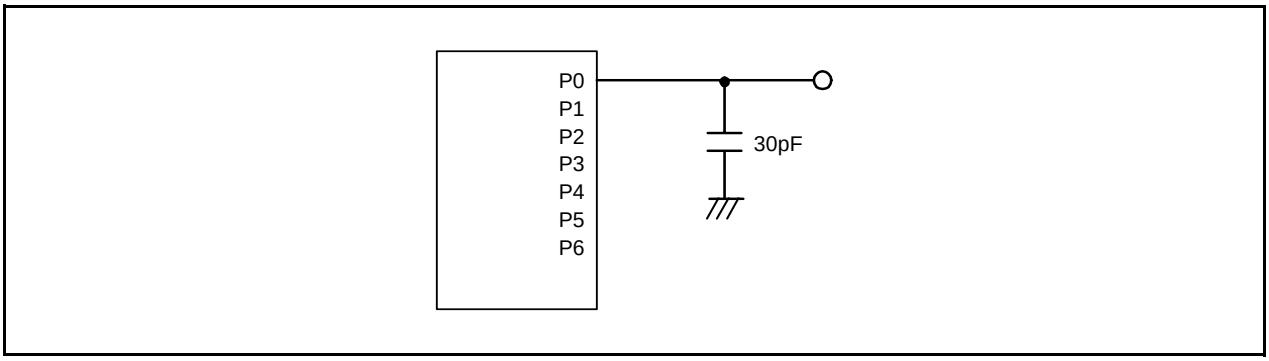


Figure 5.1 Ports P0 to P6 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}		–	–	10	Bit
–	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	–	5	MHz
–	Tolerance level impedance				–	3	–	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
I_{Vref}	V_{ref} current		V_{CC} = 5 V, XIN = f1 = ϕAD = 20 MHz		–	45	–	µA
V_{ref}	Reference voltage				2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	–	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		1,000 (3)	–	–	times
–	Byte program time		–	80	500	µs
–	Block erase time		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (7)	Ambient temperature = 55°C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60°C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (2)		10,000 (3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	160	1,500	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	300	1,500	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	1	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	5+CPU clock × 3 cycles	ms
–	Interval from erase start/restart until following suspend request		0	–	–	µs
–	Time from suspend until erase restart		–	–	30+CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30+CPU clock × 1 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (7)	–	85	°C
–	Data hold time (8)	Ambient temperature = 55 °C	20	–	–	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40°C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

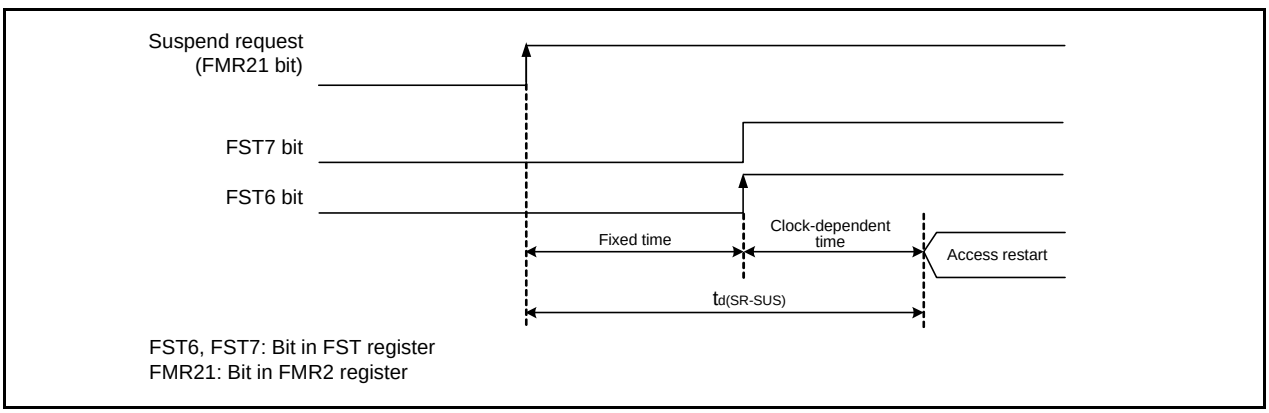


Figure 5.2 Time delay until Suspend

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
–	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5 V to (Vdet0_0 – 0.1) V	–	6	150	µs
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	1.5	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of Vcc	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of Vcc	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of Vcc	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of Vcc	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of Vcc	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of Vcc	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of Vcc	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of Vcc	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of Vcc	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of Vcc	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of Vcc	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of Vcc	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of Vcc	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of Vcc	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of Vcc	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of Vcc	4.20	4.45	4.75	V
–	Hysteresis width at the rising of Vcc in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	–	0.07	–	V
		Vdet1_6 to Vdet1_F selected	–	0.10	–	V
–	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5 V to (Vdet1_0 – 0.1) V	–	60	150	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		–	–	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 V to 5.5 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

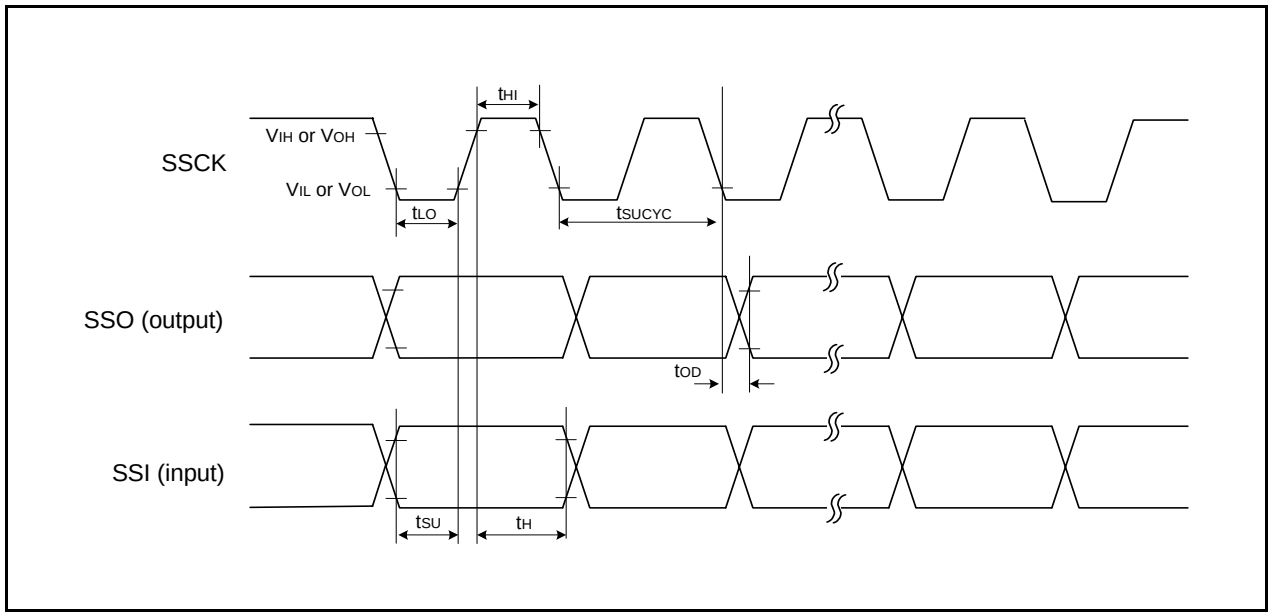


Figure 5.6 I/O Timing of Synchronous Serial Communication Unit (SSU) (Clock Synchronous Communication Mode)

Table 5.23 Electrical Characteristics (3) [2.7 V ≤ Vcc < 4.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –5 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 µA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO	V_{CC} = 3.0 V		0.1	0.4	–	V
		$\overline{RESET}$	V_{CC} = 3.0 V		0.1	0.5	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3.0 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3.0 V		–	–	–4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3.0 V		42	84	168	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

Note:
1. 2.7 V ≤ V_{CC} < 4.2 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.29 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

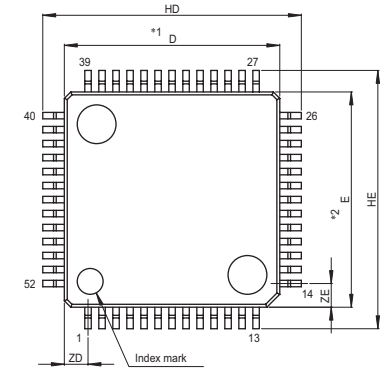
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	–	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	–	–	0.5	V
		XOUT		I_{OL} = 200 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.2	–	V
		$\overline{RESET}$			0.05	0.20	–	V
I_{IH}	Input “H” current		VI = 2.2 V, V_{CC} = 2.2 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 2.2 V		–	–	–4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			–	0.3	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	8	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

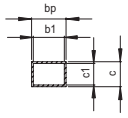
Note:
1. 1.8 V ≤ V_{CC} < 2.7 V and T_{opr} = –20 to 85°C (N version) / –40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Package Dimensions

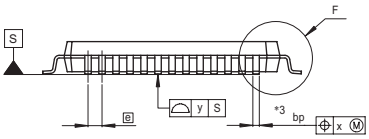
Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Electronics website.

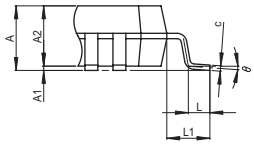
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP52-10x10-0.65	PLQP0052JA-A	52P6A-A	0.3g





Terminal cross section





Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.27	0.32	0.37
b_1	—	0.30	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
Z_D	—	1.1	—
Z_E	—	1.1	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	R8C/35C Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Sep. 01, 2009	–	First Edition issued
1.00	Aug. 24, 2010	All	“Preliminary” and “Under development” deleted
		4	Table1.3 revised
		27 to 53	5. Electrical Characteristics added

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